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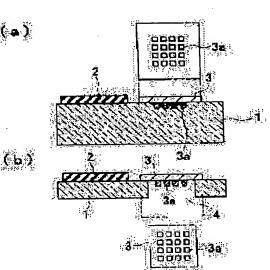
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(54) SEMICONDUCTOR DEVICE AND ITS MANUFACTURE

(57) Abstract:

PROBLEM TO BE SOLVED: To provide a manufacturing method of a semiconductor device, in which cracks and splits of a semiconductor substrate are hardly generated and alignment precision can be improved. SOLUTION: In this manufacturing method of a semiconductor device, a surface circuit pattern 2 is formed on the surface of the semiconductor device, and a pattern 3a for alignment is formed. After an alignment mark 3 for the back is formed by depositing metal or dielectrics on the pattern 3a for alignment and its peripheral region, a perpendicular through-trench 4 which reaches the alignment mark 3 for the back is formed in a region in the back of a semiconductor substrate, the region of which faces the alignment mark 3 in the back, and the alignment mark 3 for the back is exposed on the back surface side of the semiconductor substrate. The alignment mark 3 for the back is used as reference, and a circuit pattern on the back is formed.



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